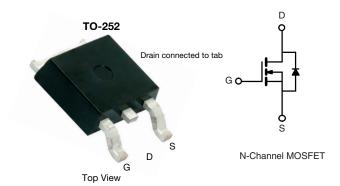


Automotive N-Channel 250 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	250			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.350			
I _D (A)	7			
Configuration	Single			
Package	TO-252			



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified d
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



FREE

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	250	V	
Gate-Source Voltage		V_{GS}	± 30	V	
Continuous Drain Current	T _C = 25 °C	- I _D	7		
	T _C = 125 °C		4		
Continuous Source Current (Diode Conduction) a		I _S	50	Α	
Pulsed Drain Current b		I _{DM}	15		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	7		
Single Pulse Avalanche Energy	L = U.1 MH	E _{AS}	2.4	mJ	
Martin or Broad Bird attack	T _C = 25 °C	D	71	10/	
Maximum Power Dissipation ^b	T _C = 125 °C	P_{D}	23	W	
Operating Junction and Storage Temperature Range		T _J , T _{sta}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount c	R _{thJA}	50	°C/W		
Junction-to-Case (Drain)		R_{thJC}	2.1	C/VV		

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	1				ı		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		250	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		3.0	3.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 30 \text{ V}$		-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 250 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 250 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 250 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α
		V _{GS} = 10 V	I _D = 10 A	-	0.290	0.350	
Drain-Source On-State Resistance a	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	-	-	0.858	Ω
		V _{GS} = 10 V	I _D = 10 A, T _J = 175 °C	-	-	1.250	
Forward Transconductance b	9 _{fs}	V _{DS}	V _{DS} = 15 V, I _D = 10 A		20	=	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	964	1205	
Output Capacitance	C _{oss}	V _{GS} = 0 V	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	88	110	pF
Reverse Transfer Capacitance	C _{rss}	1		-	32	40	
Total Gate Charge ^c	Qg			-	19	29	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 125 \text{ V}, I_D = 10 \text{ A}$	-	6.5	-	nC
Gate-Drain Charge ^c	Q_{gd}	1		-	5	-	
Gate Resistance	R_g		f = 1 MHz		1	3	Ω
Turn-On Delay Time ^c	t _{d(on)}				9	14	
Rise Time ^c	t _r	V_{DD} = 125 V, R_L = 12.5 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω		-	8	12	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	15	23	
Fall Time ^c	t _f			-	4	6	
Source-Drain Diode Ratings and Chara	cteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	15	Α
Forward Voltage	V _{SD}	I _F = 20 A, V _{GS} = 0 V		_	0.9	1.5	V

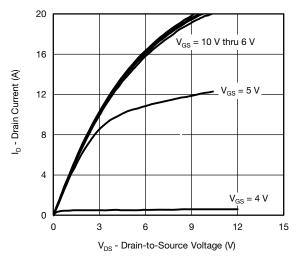
Notes

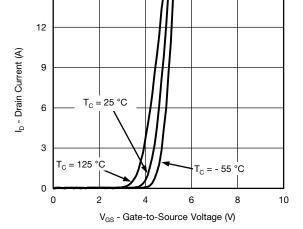
- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



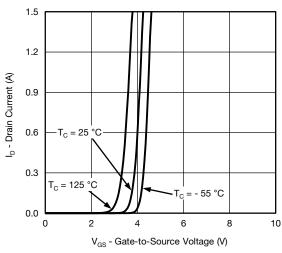
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

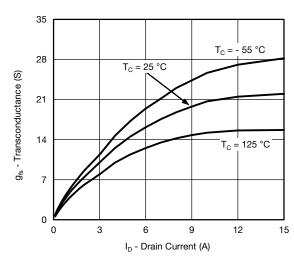




Output Characteristics

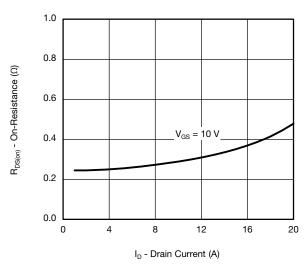
Transfer Characteristics

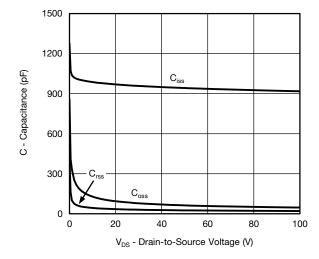




Transfer Characteristics

Transconductance





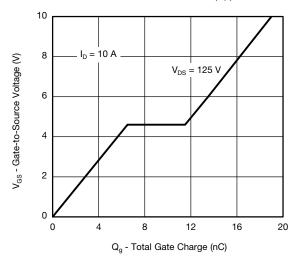
On-Resistance vs. Drain Current

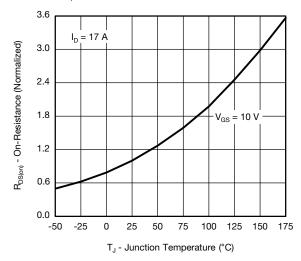
Capacitance

For technical questions, contact: automostechsu



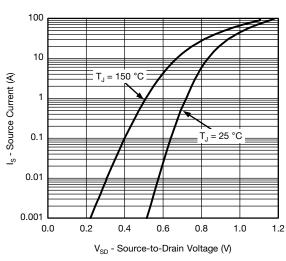
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

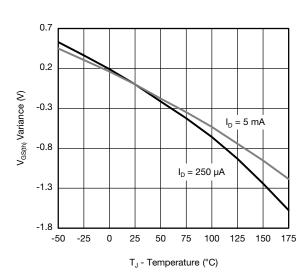




Gate Charge

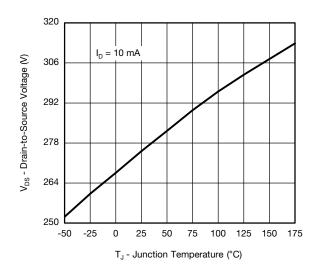






Source Drain Diode Forward Voltage

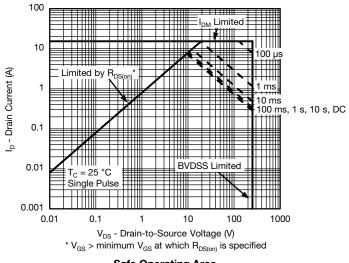
Threshold Voltage



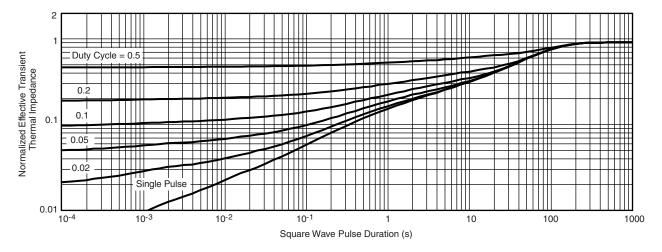
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)

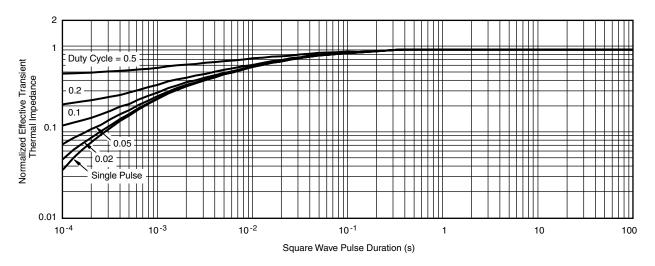


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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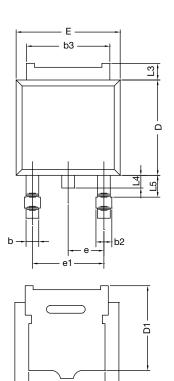
REVISION HISTORY ^a				
REVISION	DATE	DESCRIPTION OF CHANGE		
С	04-Aug-15	Revised R _g minimum limit		

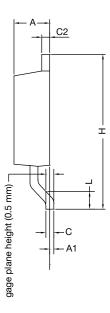
Note

a. As of April 2014



TO-252AA Case Outline





	MILLIN	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019					

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE



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